

R-C Thermal Model Parameters

DESCRIPTION

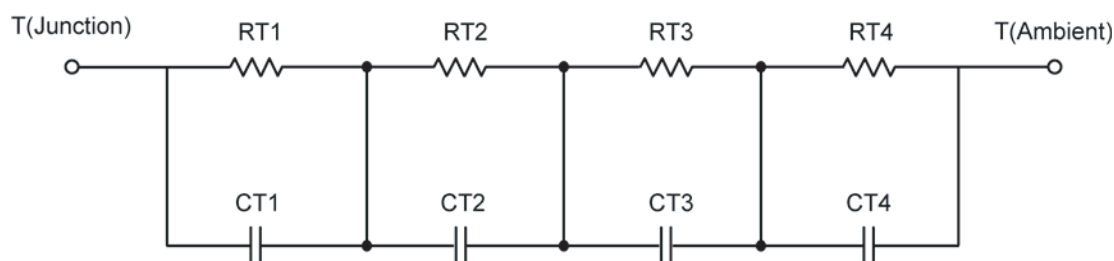
The parametric values in the R-C thermal model have been derived using curve-fitting techniques. These techniques are described in "[A Simple Method of Generating Thermal Models for a Power MOSFET](#)"[1]. When implemented in P-Spice, these values have matching characteristic curves to the Single Pulse Transient Thermal Impedance curves for the MOSFET.

R-C values for the electrical circuit in the Foster/Tank and Cauer/Filter configurations are included.

Note:

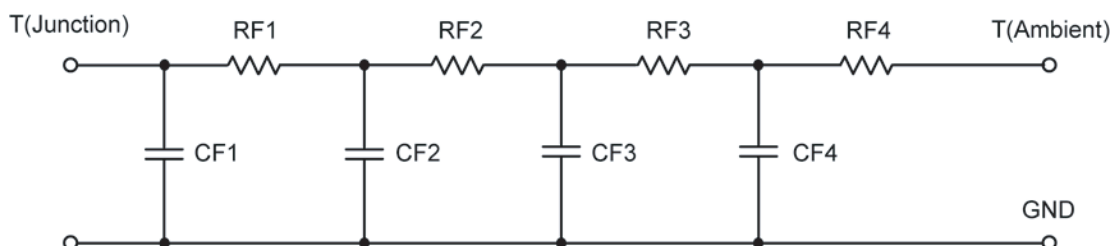
For a detailed explanation of implementing these values in P-SPICE, refer to [Application Note AN609 Thermal Simulations Of Power MOSFETs on P-SPICE Platform](#).

R-C THERMAL MODEL FOR TANK CONFIGURATION



R-C VALUES FOR TANK CONFIGURATION			
Thermal Resistance (°C/W)			
Junction to	Ambient	Case	Foot
RT1	20.4479	N/A	13.9489
RT2	5.2285	N/A	3.6892
RT3	35.2771	N/A	14.6643
RT4	48.7310	N/A	8.7285
Thermal Capacitance (Joules/°C)			
Junction to	Ambient	Case	Foot
CT1	5.8305 m	N/A	4.2521 m
CT2	567.4529 u	N/A	519.4117 u
CT3	29.9527 m	N/A	27.4798 m
CT4	1.0281	N/A	132.2231 m

This document is intended as a SPICE modeling guideline and does not constitute a commercial product data sheet. Designers should refer to the appropriate data sheet of the same number for guaranteed specification limits.

R-C THERMAL MODEL FOR FILTER CONFIGURATION**R-C VALUES FOR FILTER CONFIGURATION**

Thermal Resistance ($^{\circ}\text{C}/\text{W}$)			
Junction to	Ambient	Case	Foot
RF1	7.1285	N/A	4.8368
RF2	27.1298	N/A	18.1843
RF3	29.7839	N/A	15.7594
RF4	45.7593	N/A	2.4026
Thermal Capacitance (Joules/ $^{\circ}\text{C}$)			
Junction to	Ambient	Case	Foot
CF1	613.9002 u	N/A	455.8803 u
CF2	4.4775 m	N/A	3.3508 m
CF3	32.7783 m	N/A	26.9370 m
CF4	1.0895	N/A	618.6570 m

Note: NA indicates not applicable

Reference:

[1] "A Simple Method of Generating Thermal Models for a Power MOSFET" by Wharton McDaniel and Kandarp Pandya. IEEE / SEMITHERM 2002

